

# BRCS060N03ZC

Rev.B May.-2021

## 描述 / Descriptions

PDFN5\*6 封装 N 沟道场效应管。

N-Channel MOSFET in a PDFN5\*6 Plastic Package .

## 特征 / Features

低电阻可最大地降低导电损耗；低栅极电荷，可实现快速切换；低热阻。

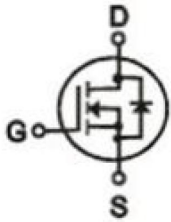
Low  $R_{DS(ON)}$  to minimize conductive loss; low Gate Charge for fast switching; Low Thermal resistance.

## 用途 / Applications

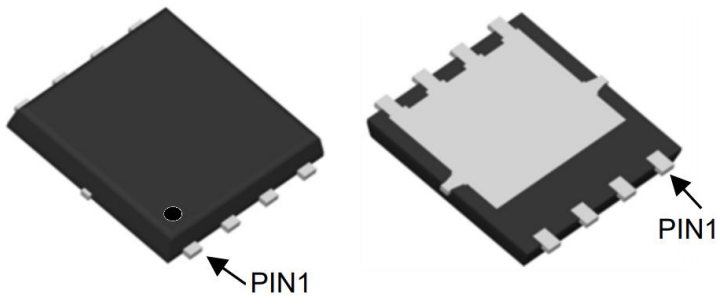
电池管理

Battery Management

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1、2、3: S    PIN4: G    PIN5、6、7、8: D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings( $T_a=25^{\circ}\text{C}$ )**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit	
Drain-Source Voltage	$V_{DS}$	30	V	
Drain Current - Continuous	$I_D$	45	A	
Drain Current – Pulsed	$I_{DM}$	135	A	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Power Dissipation	$P_D(T_c=25^{\circ}\text{C})$	28	W	
Single Pulse Avalanche Energy(L=0.5mH)	$E_{AS}$	211	mJ	
Avalanche Current(L=0.5mH)	$I_{AS}$	23	A	
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^{\circ}\text{C}$	
Thermal resistance, junction - ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	36	$^{\circ}\text{C/W}$
	Steady-State		64.8	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	4.5	

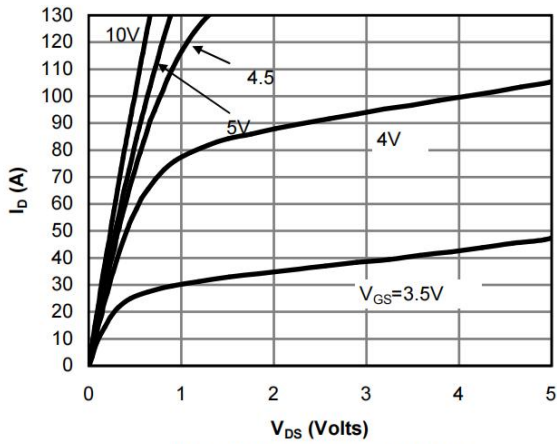
**电性能参数 / Electrical Characteristics( $T_a=25^{\circ}\text{C}$ )**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30	33		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			1.0	$\mu\text{A}$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=20\text{A}$		4.5	6	m $\Omega$
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		7	9	
Input Capacitance	$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		2090		pF
Output Capacitance	$C_{oss}$			790		
Reverse Transfer Capacitance	$C_{rss}$				634	
Gate resistance	$R_g$	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		1.9		$\Omega$
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}, V_{DS}=15\text{V}$ $I_D=20\text{A}$		37		nC
Total Gate Charge	$Q_g(4.5\text{V})$			18		
Gate Source Charge	$Q_{gs}$			4.8		
Gate Drain Charge	$Q_{gd}$			11		

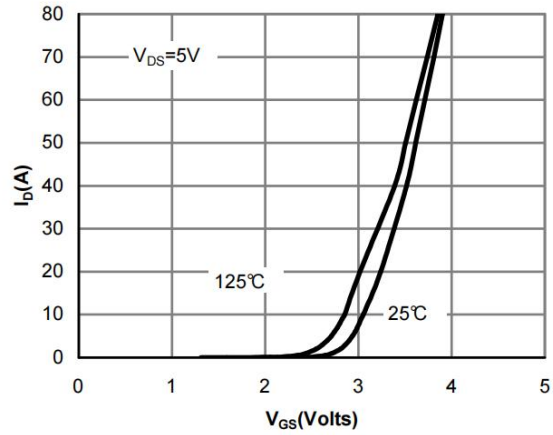
## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V,$ $R_L=0.75\Omega, R_{GEN}=3\Omega$		8.1		ns
Turn-On Rise Time	$t_r$			8.6		
Turn-Off Delay Time	$t_{D(off)}$			29		
Turn-Off Fall Time	$t_f$			8		

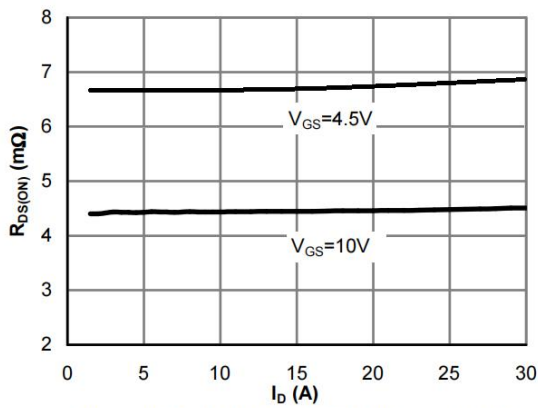
**电参数曲线图 / Electrical Characteristic Curve**



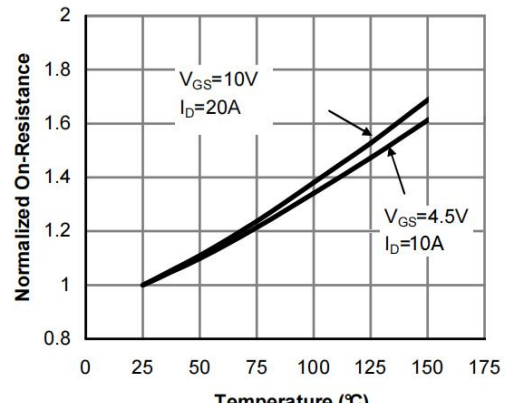
**Fig 1: On-Region Characteristics**



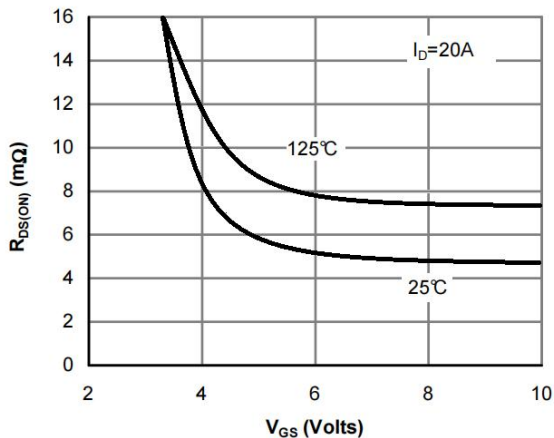
**Figure 2: Transfer Characteristics**



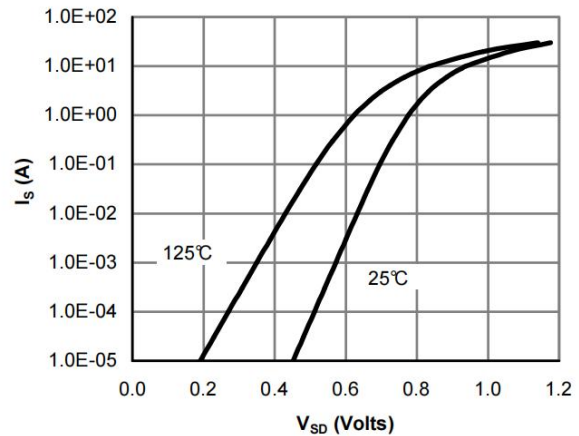
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5: On-Resistance vs. Gate-Source Voltage**



**Figure 6: Body-Diode Characteristics**

**电参数曲线图 / Electrical Characteristic Curve**

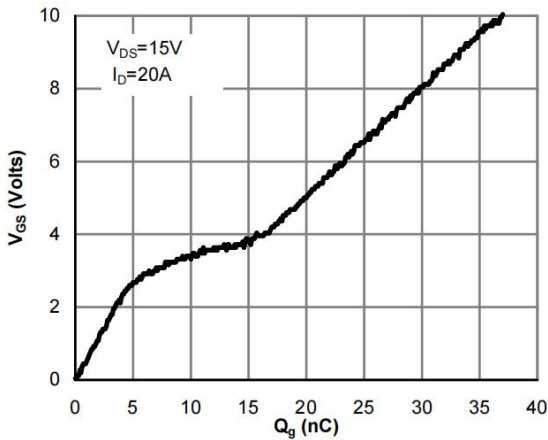


Figure 7: Gate-Charge Characteristics

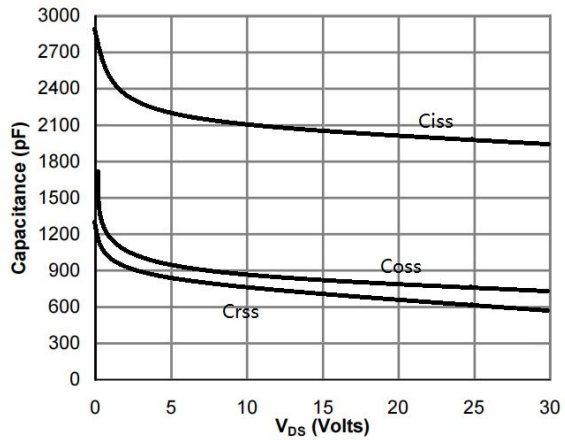


Figure 8: Capacitance Characteristics

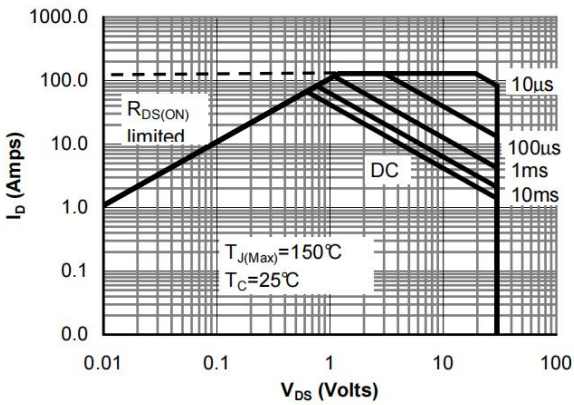


Figure 9: Maximum Forward Biased Safe Operating Area

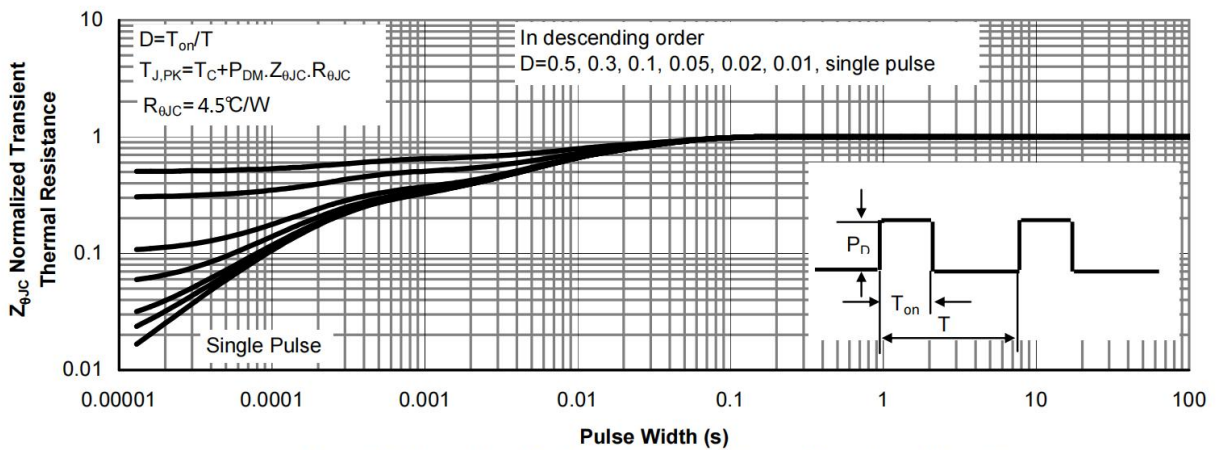
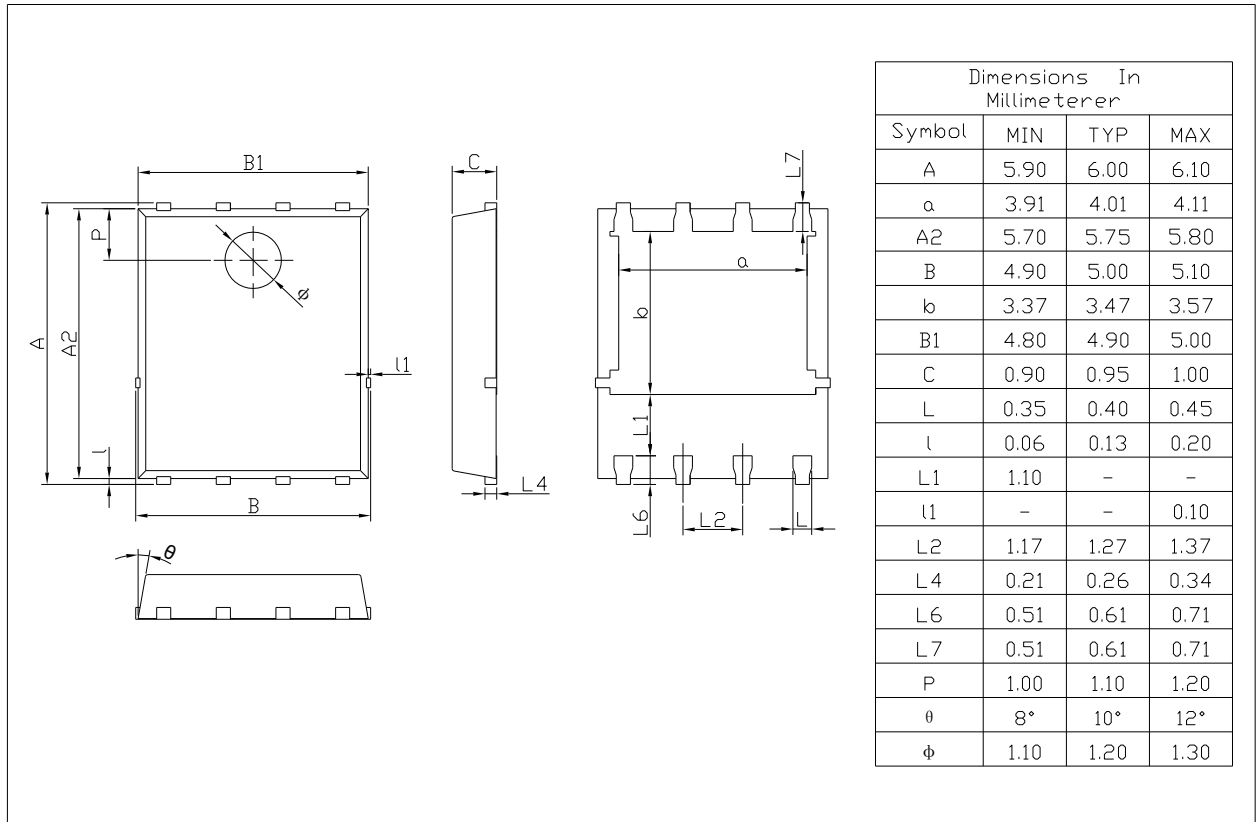


Figure 10: Normalized Maximum Transient Thermal Impedance (Note F)

**外形尺寸图 / Package Dimensions**

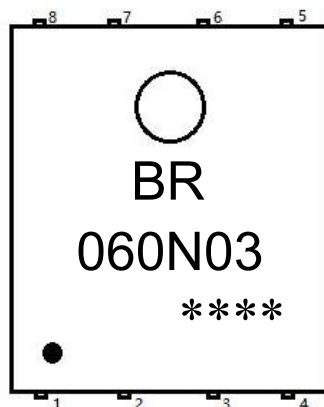
PDFN5 X6

Unit:mm



Rev.00 201812

**印章说明 / Marking Instructions**



说明：

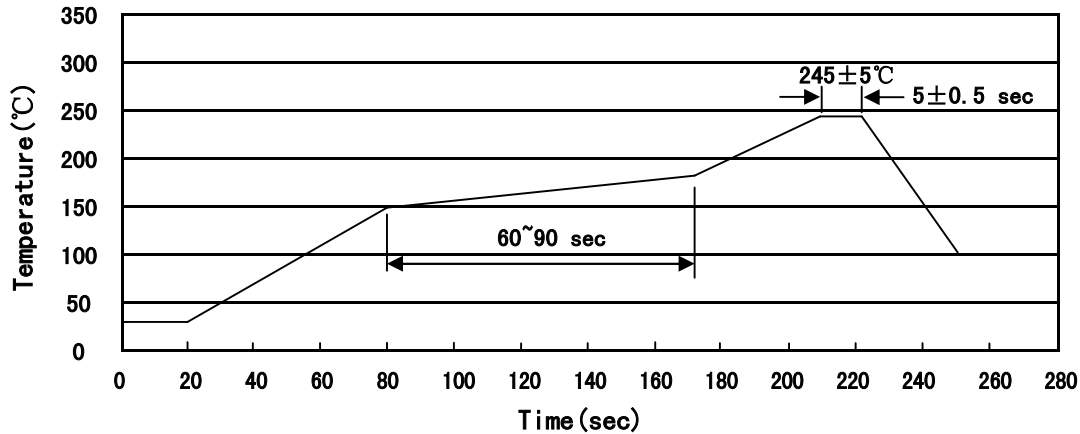
BR： 为公司代码

060N03： 为为产品型号

Note：

BR： Company Code

060N03： Product Type.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

**使用说明 / Notices**



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